ALPHA & OMEGA SEMICONDUCTOR

AOSS21115C

20V P-Channel MOSFET

General Description

- Trench Power MOSFET technology
- Low $R_{DS(ON)}$
- Low Gate Charge
- RoHS and Halogen-Free Compliant

Applications

- This device is ideal for Load Switch

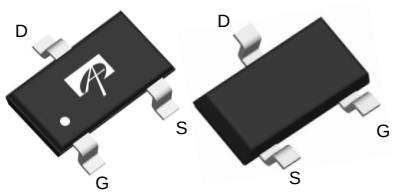
Product Summary

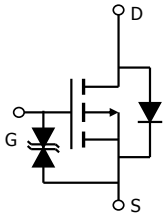
V_{DS}	-20V
I_D (at V_{GS}=-4.5V)	-4.5A
$R_{DS(ON)}$ (at V_{GS}=-4.5V)	< 40mΩ
$R_{DS(ON)}$ (at V_{GS}=-2.5V)	< 55mΩ
$R_{DS(ON)}$ (at V_{GS}=-1.8V)	< 72mΩ
Typical ESD protection	**HBM Class 2**

Green Product

SOT23

Top View **Bottom View**





Orderable Part Number	Package Type	Form	Minimum Order Quantity
AOSS21115C	SOT23-3	Tape & Reel	3000

Absolute Maximum Ratings T_A=25°C unless otherwise noted

Parameter		Symbol	Maximum	Units
Drain-Source Voltage		V_{DS}	-20	V
Gate-Source Voltage		V_{GS}	±8	V
Continuous Drain Current	T_A=25°C	I_D	-4.5	A
	T_A=70°C		-3.5	
Pulsed Drain Current [C]		I_{DM}	-18	
Power Dissipation [B]	T_A=25°C	P_D	1.3	W
	T_A=70°C		0.8	
Junction and Storage Temperature Range		T_J, T_{STG}	-55 to 150	°C

Thermal Characteristics

Parameter		Symbol	Typ	Max	Units
Maximum Junction-to-Ambient [A]	t ≤ 10s	$R_{\theta JA}$	70	90	°C/W
Maximum Junction-to-Ambient [A D]	Steady-State		100	125	°C/W
Maximum Junction-to-Lead	Steady-State	$R_{\theta JL}$	63	80	°C/W

Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV_{DSS}	Drain-Source Breakdown Voltage	I_D=-250µA, V_{GS}=0V	-20			V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=-20V, V_{GS}=0V			-1	µA
		T_J=55°C			-5	
I_{GSS}	Gate-Body leakage current	V_{DS}=0V, V_{GS}=±8V			±10	µA
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_D=-250µA	-0.15	-0.55	-0.95	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS}=-4.5V, I_D=-4.5A		33	40	mΩ
		T_J=125°C		43	52	
		V_{GS}=-2.5V, I_D=-4A		42	55	mΩ
		V_{GS}=-1.8V, I_D=-3.5A		54	72	mΩ
g_{FS}	Forward Transconductance	V_{DS}=-5V, I_D=-4.5A		20		S
V_{SD}	Diode Forward Voltage	I_S=-1A, V_{GS}=0V		-0.7	-1	V
I_S	Maximum Body-Diode Continuous Current				-2	A
DYNAMIC PARAMETERS						
C_{iss}	Input Capacitance	V_{GS}=0V, V_{DS}=-10V, f=1MHz		930		pF
C_{oss}	Output Capacitance			90		pF
C_{rss}	Reverse Transfer Capacitance			80		pF
R_g	Gate resistance	f=1MHz		15	30	Ω
SWITCHING PARAMETERS						
Q_g(4.5V)	Total Gate Charge	V_{GS}=-4.5V, V_{DS}=-10V, I_D=-4.5A		8.5	17	nC
Q_{gs}	Gate Source Charge			1		nC
Q_{gd}	Gate Drain Charge			2.5		nC
$t_{D(on)}$	Turn-On DelayTime	V_{GS}=-4.5V, V_{DS}=-10V, R_L=2.22Ω, R_{GEN}=3Ω		12		ns
t_r	Turn-On Rise Time			11		ns
$t_{D(off)}$	Turn-Off DelayTime			82		ns
t_f	Turn-Off Fall Time			35		ns
t_{rr}	Body Diode Reverse Recovery Time	I_F=-4.5A, di/dt=500A/µs		25		ns
Q_{rr}	Body Diode Reverse Recovery Charge	I_F=-4.5A, di/dt=500A/µs		37		nC

A. The value of $R_{\theta JA}$ is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with T_A =25° C. The value in any given application depends on the user's specific board design.
B. The power dissipation P_D is based on $T_{J(MAX)}$=150° C, using ≤ 10s junction-to-ambient thermal resistance.
C. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}$=150° C. Ratings are based on low frequency and duty cycles to keep initialT_J=25° C.
D. The $R_{\theta JA}$ is the sum of the thermal impedance from junction to lead $R_{\theta JL}$ and lead to ambient.
E. The static characteristics in Figures 1 to 6 are obtained using <300µs pulses, duty cycle 0.5% max.
F. These curves are based on the junction-to-ambient thermal impedance which is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, assuming a maximum junction temperature of $T_{J(MAX)}$=150° C. The SOA curve provides a single pulse rating.

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

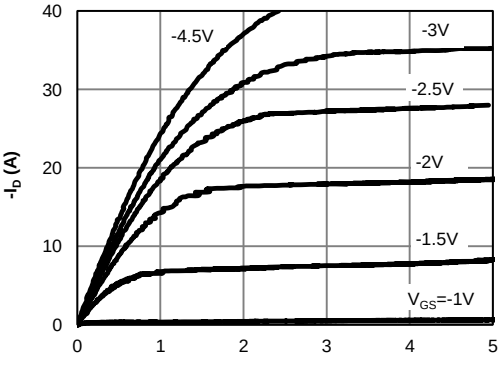


Figure 1: On-Region Characteristics (Note E)

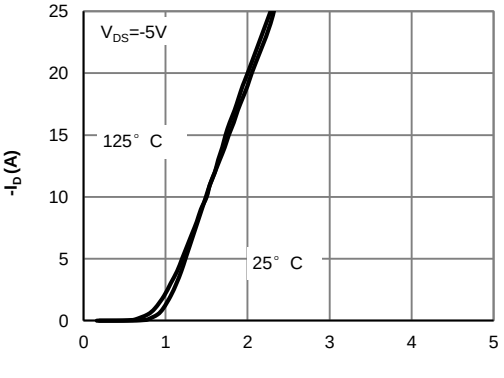


Figure 2: Transfer Characteristics (Note E)

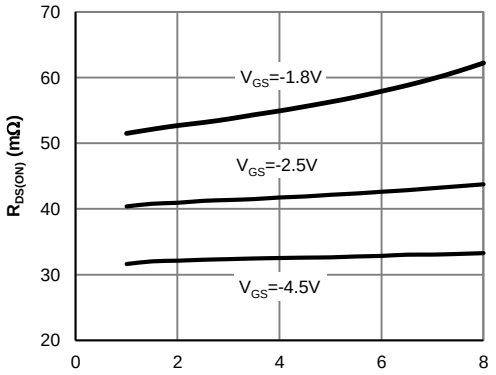


Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

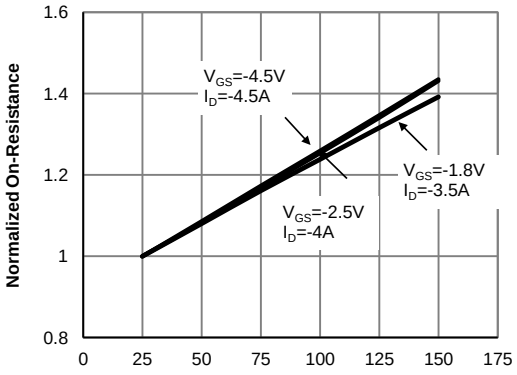


Figure 4: On-Resistance vs. Junction Temperature (Note E)

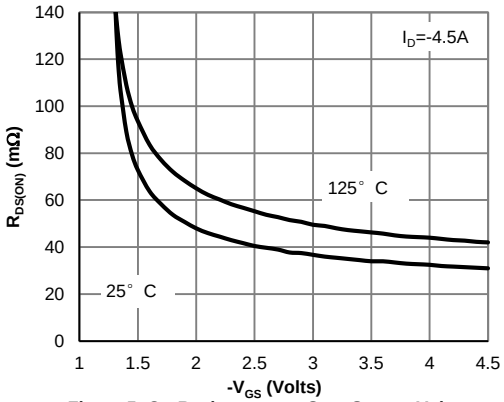


Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

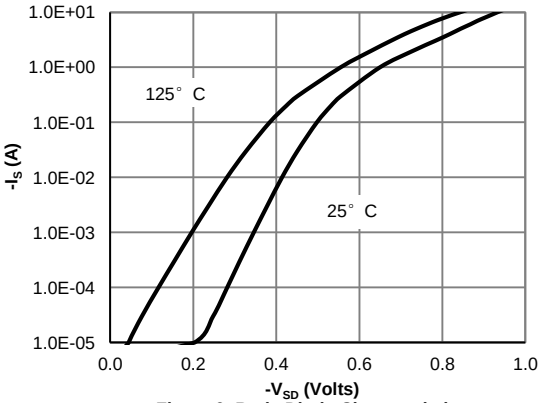


Figure 6: Body-Diode Characteristics (Note E)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

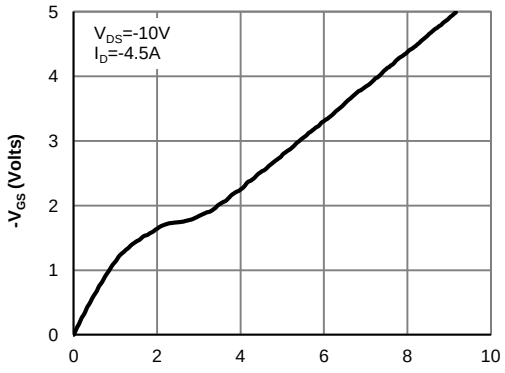


Figure 7: Gate-Charge Characteristics

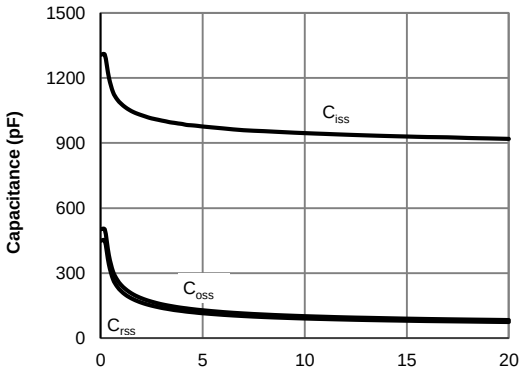
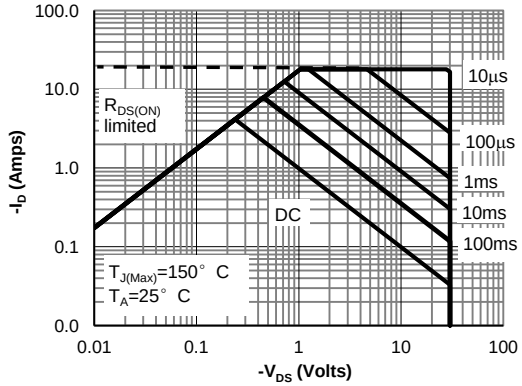


Figure 8: Capacitance Characteristics



V_{GS}> or equal to -1.8V
Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

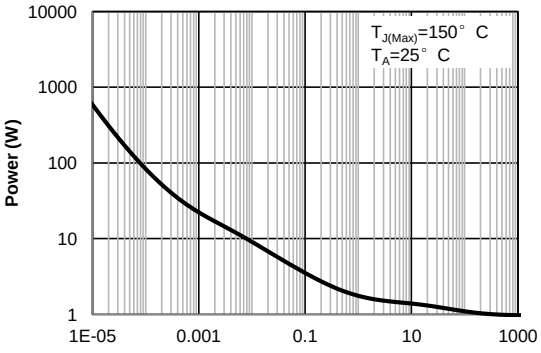


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note F)

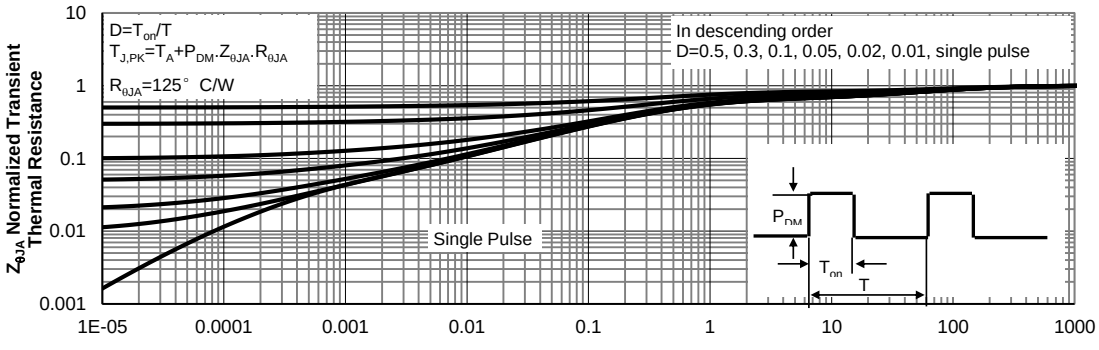
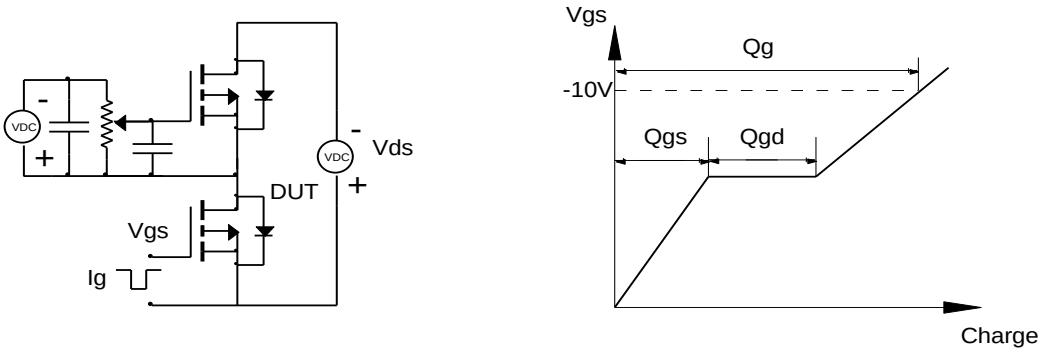
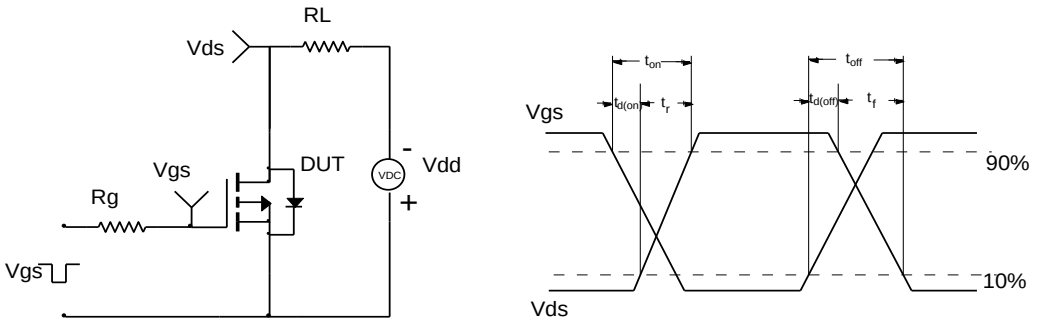


Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)

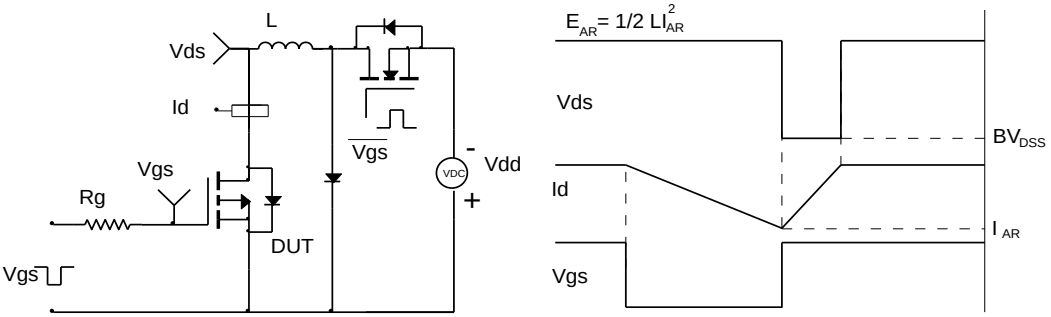
Gate Charge Test Circuit & Waveform



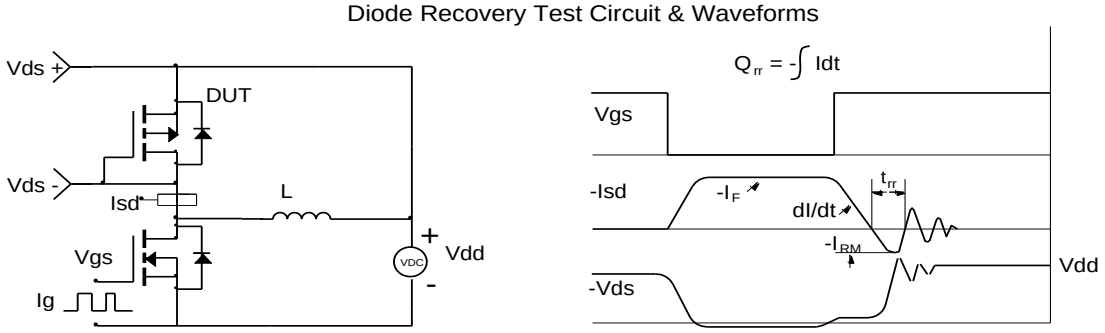
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



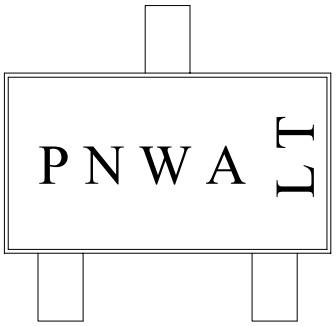
Diode Recovery Test Circuit & Waveforms



ALPHA & OMEGA SEMICONDUCTOR

Document No.	PD-03215
Version	B
Title	AOSS21115C Marking Description

SOT-23 PACKAGE MARKING DESCRIPTION



Green product

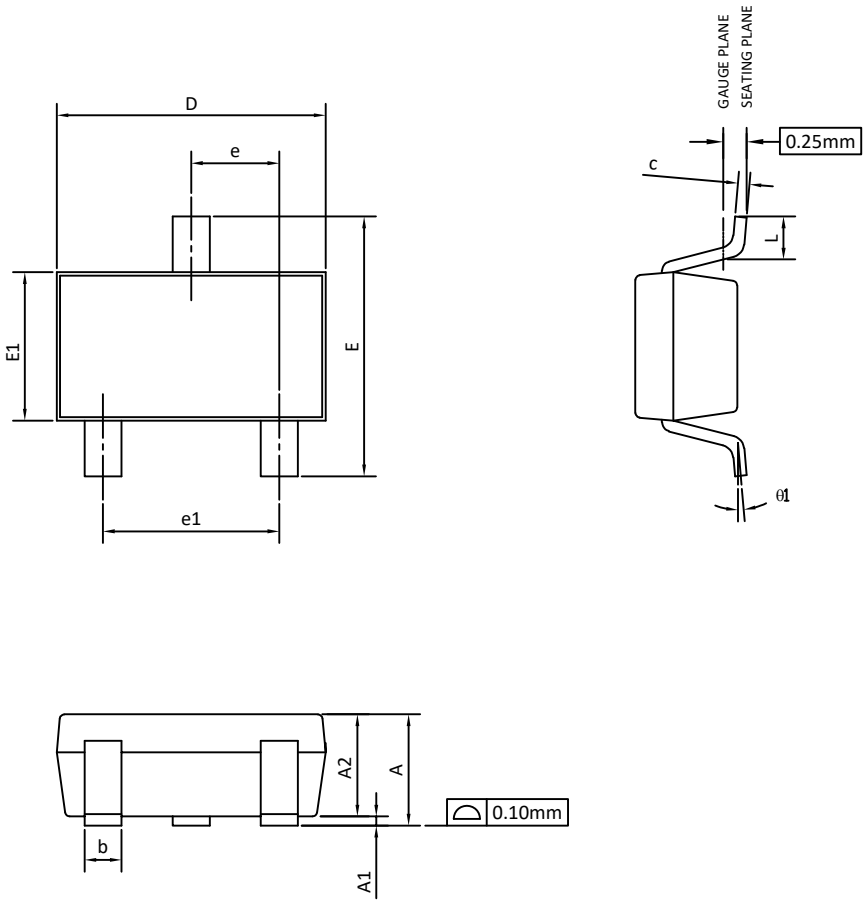
NOTE:
PN - Part number code
W - Year and week code
A - Assembly location code
L&T - Assembly lot code

PART NO.	DESCRIPTION	CODE (PN)
AOSS21115C	Green product	LP

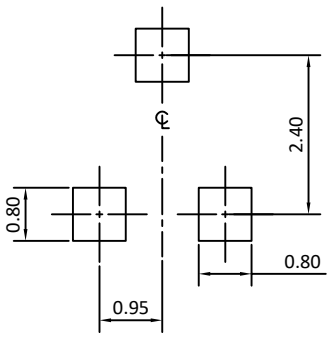
ALPHA & OMEGA SEMICONDUCTOR

Document No.	PO-00001
Version	N

SOT23 PACKAGE OUTLINE



RECOMMENDED LAND PATTERN



UNIT: mm

SYMBOLS	DIMENSION IN MM			DIMENSION IN INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.85	---	1.25	0.033	----	0.049
A1	0.00	---	0.15	0.000	----	0.006
A2	0.70	1.05	1.20	0.028	0.041	0.047
b	0.30	0.40	0.50	0.012	0.016	0.020
c	0.08	0.13	0.20	0.003	0.005	0.008
D	2.80	2.90	3.10	0.110	0.114	0.122
e	0.95 BSC			0.037 BSC		
e1	1.90 BSC			0.075 BSC		
E	2.60	2.80	3.00	0.102	0.110	0.118
E1	1.40	1.60	1.80	0.055	0.063	0.071
L	0.30	---	0.60	0.012	----	0.024
Q1	0°	5°	8°	0°	5°	8°

NOTE:

1. PACKAGE BODY SIZES EXCLUDE MOLD FLASH OR GATE BURRS.
   MOLD FLASH AT THE NON-LEAD SIDES SHOULD BE LESS THAN 5 MILS EACH.
2. TOLERANCE ±0.100 mm (4 mil) UNLESS OTHERWISE SPECIFIED.
3. DIMENSION L IS MEASURED IN GAUGE PLANE.
4. CONTROLLING DIMENSION IS MILLIMETER. CONVERTED INCH DIMENSIONS
   ARE NOT NECESSARILY EXACT.
5. ALL DIMENSIONS ARE IN MILLIMETERS.

ALPHA & OMEGA SEMICONDUCTOR

AOS Semiconductor
Product Reliability Report

AOSS21115C, rev A

Plastic Encapsulated Device

ALPHA & OMEGA Semiconductor, Inc

www.aosmd.com

Jun, 2019

ALPHA & OMEGA SEMICONDUCTOR

This AOS product reliability report summarizes the qualification result for AOSS21115C. Accelerated environmental tests are performed on a specific sample size, and then followed by electrical test at end point. Review of final electrical test result confirms that AOSS21115C passes AOS quality and reliability requirements. The released product will be categorized by the process family and be routine monitored for continuously improving the product quality.

I. Reliability Stress Test Summary and Results

Test Item	Test Condition	Time Point	Total Sample Size	Number of Failures	Reference Standard
HTGB	Temp = 150°C , Vgs=100% of Vgsmax	168 / 500 / 1000 hours	462 pcs	0	JESD22-A108
HTRB	Temp = 150°C , Vds=100% of Vdsmax	168 / 500 / 1000 hours	462 pcs	0	JESD22-A108
Precondition (Note A)	168hr 85°C / 85%RH + 3 cycle reflow@260°C (MSL 1)	-	4620 pcs	0	JESD22-A113
HAST	130°C , 85%RH, 33.3 psia, Vds = 80% of Vdsmax	96 hours	693 pcs	0	JESD22-A110
H3TRB	85°C , 85%RH, Vds = 80% of Vdsmax	1000 hours	693 pcs	0	JESD22-A101
Autoclave	121°C , 29.7psia, RH=100%	96 hours	924 pcs	0	JESD22-A102
Temperature Cycle	-65°C to 150°C , air to air,	1000cycles	924 pcs	0	JESD22-A104
HTSL	Temp = 150°C	1000 hours	693 pcs	0	JESD22-A103
IOL	∆ Tj = 100°C	15000 cycles	693 pcs	0	MIL-STD-750 Method 1037

Note: The reliability data presents total of available generic data up to the published date.
Note A: MSL (Moisture Sensitivity Level) 1 based on J-STD-020

II. Reliability Evaluation

FIT rate (per billion): 3.82
MTTF = 29919 years

The presentation of FIT rate for the individual product reliability is restricted by the actual burn-in sample size. Failure Rate Determination is based on JEDEC Standard JESD 85. FIT means one failure per billion hours.

Failure Rate = $Chi^2 \times 10^9$ **/ [**2 (N) (H) (Af)**] =** 3.82
MTTF = 10^9 / FIT = 29919 years
Chi² = Chi Squared Distribution, determined by the number of failures and confidence interval
N = Total Number of units from burn-in tests
H = Duration of burn-in testing
Af = Acceleration Factor from Test to Use Conditions (Ea = 0.7eV and Tuse = 55°C)
Acceleration Factor [**Af**] = **Exp** [Ea / **k** (1/Tj u – 1/Tj s)]

Acceleration Factor ratio list:

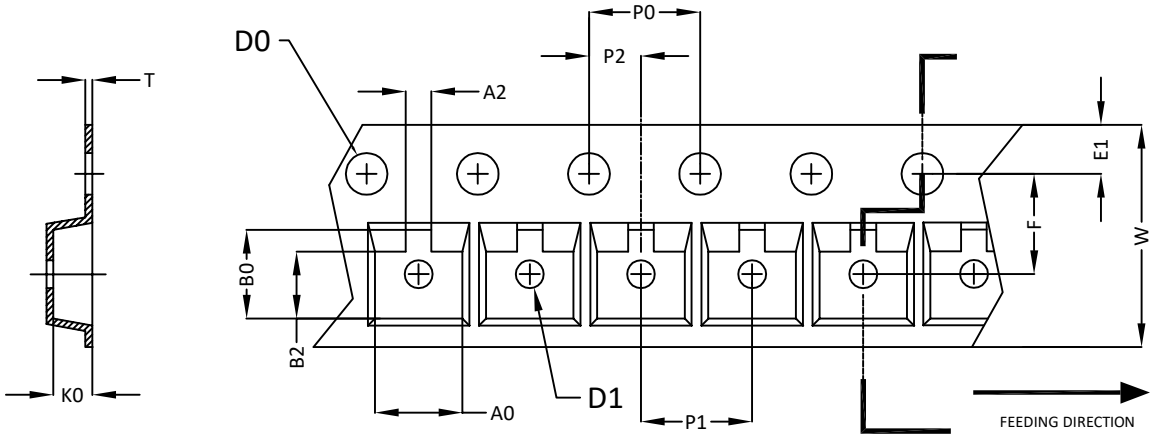
	55 deg C	70 deg C	85 deg C	100 deg C	115 deg C	130 deg C	150 deg C
Af	259	87	32	13	5.64	2.59	1

Tj s = Stressed junction temperature in degree (Kelvin), K = C+273.16
Tj u =The use junction temperature in degree (Kelvin), K = C+273.16
k = Boltzmann's constant, 8.617164 X 10^{-5}eV / K

ALPHA & OMEGA SEMICONDUCTOR

SOT23 Tape and Reel Data

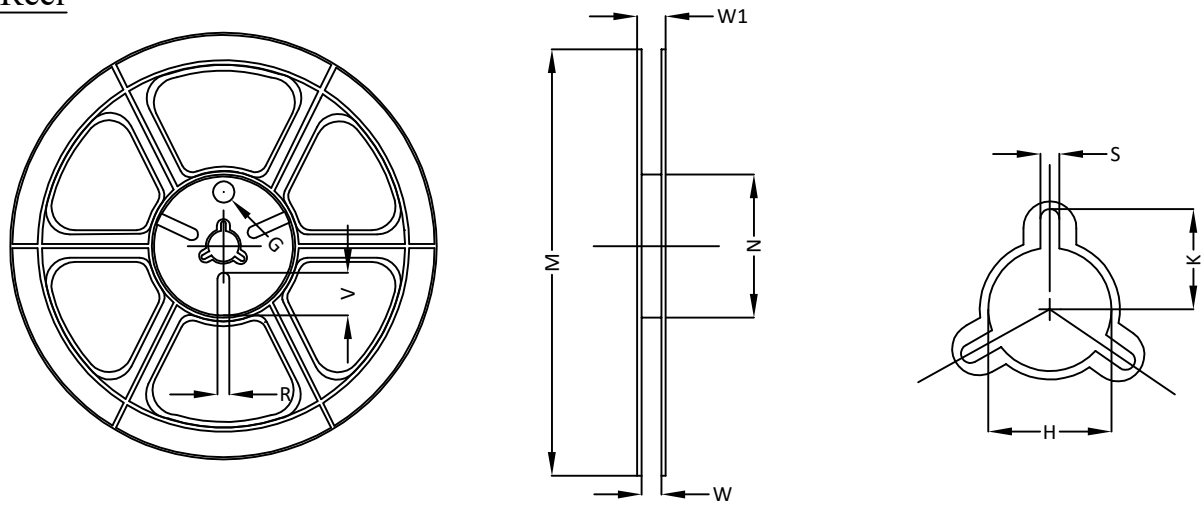
SOT23 Carrier Tape



UNIT: MM

PACKAGE	A0	B0	K0	D0	D1	W	E1	F	P0	P1	P2	T	A2	B2
SOT23-3L (8 mm)	3.05 -3.40	3.00-3.38	1.20- 1.47	1.55 ±0.05	1.00 ±0.25	8.00 ±0.30	1.75 ±0.10	3.50 ±0.05	4.00 ±0.10	4.00 ±0.10	2.00 ±0.05	0.18 -0.25	0.84-1.24	2.29-2.69

SOT23 Reel



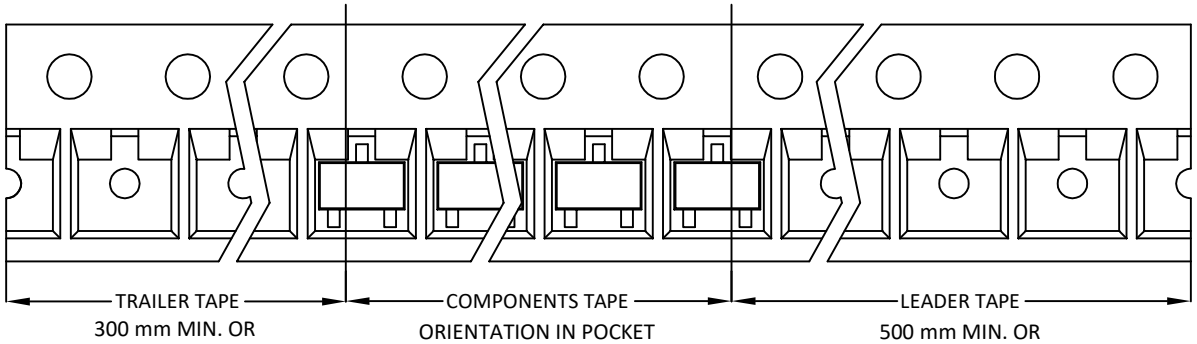
UNIT: MM

TAPE SIZE	REEL SIZE	M	N	W	W1	H	K	S	G	R	V
8 mm	Ø178	Ø178.00 ±1.00	Ø54.00 ±0.50	9.00 ±0.30	11.40 ±1.00	Ø13.00 +0.50 -0.20	10.60	2.00 ±0.50	Ø9.00	5.00	18.00

SOT23 Tape

Leader / Trailer & Orientation

Unit Per Reel: 3000pcs



All Dimensions Comply with EAI-481